SamHop Microelectronics Corp.

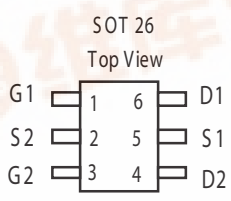
STS3621

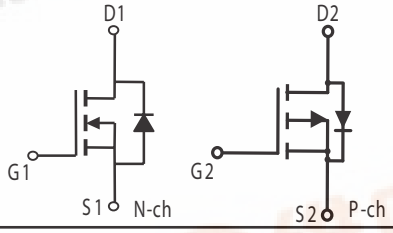
Oct. 24 2006

Dual Enhancement Mode Field Effect Transistor (N and P Channel)

PRODUCT SUMMARY (N-Channel)		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ) Max
30V	3A	50 @ V_{GS} = 10V
		65 @ V_{GS} = 4.5V

PRODUCT SUMMARY (P-Channel)		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ) Max
-30V	-2A	90 @ V_{GS} = -10V
		135 @ V_{GS} = -4.5V





ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V_{DS}	30	-30	V
Gate-Source Voltage		V_{GS}	±20	±20	V
Drain Current-Continuous [a] @ Ta	25°C	I_D	3	-2	A
	70°C		2.7	1.8	A
-Pulsed [b]		I_{DM}	12	-8	A
Drain-Source Diode Forward Current [a]		I_S	1.25	-1.25	A
Maximum Power Dissipation [a]	Ta= 25°C	P_D	1.25		W
	Ta=70°C		0.8		
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150		°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient [a]	$R_{\theta JA}$	100	°C/W

STS3621

N-Channel ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ [C]	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250uA	30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=24V, V_{GS}=0V			1	uA
Gate-Body Leakage	I_{GSS}	V_{GS}=± 20V, V_{DS}=0V			±100	nA
ON CHARACTERISTICS [b]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1	1.7	3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=3A		40	50	m-ohm
		V_{GS}=4.5V, I_D=2A		52	65	m-ohm
On-State Drain Current	$I_{D(ON)}$	V_{DS}=5V, V_{GS}=4.5V	10			A
Forward Transconductance	g_{FS}	V_{DS}=5V, I_D=3A		9		S
DYNAMIC CHARACTERISTICS [c]						
Input Capacitance	C_{ISS}	V_{DS}=15V, V_{GS}=0V f=1.0MHz		330		pF
Output Capacitance	C_{OSS}			70		pF
Reverse Transfer Capacitance	C_{RSS}			45		pF
SWITCHING CHARACTERISTICS [c]						
Turn-On Delay Time	$t_{D(ON)}$	V_{DD}=15V, I_D=1A, V_{GS}=10V, R_{GEN}=6 ohm		9		ns
Rise Time	t_r			9		ns
Turn-Off Delay Time	$t_{D(OFF)}$			15		ns
Fall Time	t_f			10		ns
Total Gate Charge	Q_g	V_{DS}=15V, I_D=3A, V_{GS}=10V		6		nC
		V_{DS}=15V, I_D=3A, V_{GS}=4.5V		3		nC
Gate-Source Charge	Q_{gs}	V_{DS}=15V, I_D=3A V_{GS}=10V		1		nC
Gate-Drain Charge	Q_{gd}			1.5		nC

STS3621

P-Channel ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ [c]	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=-250uA	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-24V, V_{GS}=0V			-1	uA
Gate-Body Leakage	I_{GSS}	V_{GS}=±20V, V_{DS}=0V			±100	nA
ON CHARACTERISTICS [b]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250uA	-1	-1.8	-3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-2A		75	90	m-ohm
		V_{GS}=-4.5V, I_D=-1A		120	135	m-ohm
On-State Drain Current	$I_{D(ON)}$	V_{DS}=-5V, V_{GS}=-10V	8			A
Forward Transconductance	g_{FS}	V_{DS}=-5V, I_D=-3A		5.5		S
DYNAMIC CHARACTERISTICS [c]						
Input Capacitance	C_{ISS}	V_{DS}=-15V, V_{GS}=0V f=1.0MHz		360		pF
Output Capacitance	C_{OSS}			84		pF
Reverse Transfer Capacitance	C_{RSS}			52		pF
SWITCHING CHARACTERISTICS [c]						
Turn-On Delay Time	$t_{D(ON)}$	V_{DD}=-15V, I_D=-1A, V_{GEN}=-10V, R_{GEN}=6 ohm		6		ns
Rise Time	t_r			9.5		ns
Turn-Off Delay Time	$t_{D(OFF)}$			48		ns
Fall Time	t_f			25		ns
Total Gate Charge	Q_g	V_{DS}=-15V,I_D=-2A,V_{GS}=-10V		7		nC
		V_{DS}=-15V,I_D=-2A,V_{GS}=-4.5V		3.4		nC
Gate-Source Charge	Q_{gs}	V_{DS}=-15V, I_D=-2A V_{GS}=-10V		0.9		nC
Gate-Drain Charge	Q_{gd}			2.2		nC

STS3621

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition		Min	Typ [c]	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS [b]							
Diode Forward Voltage	V_{SD}	V_{GS} = 0V, Is =1.25A	N-Ch		0.81	1.2	V
		V_{GS} = 0V, Is =-1.25A	P-Ch		-0.8	-1.2	

Notes

a.Surface Mounted on FR4 Board, t <=10sec.

b.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.

c.Guaranteed by design, not subject to production testing.

N-Channel

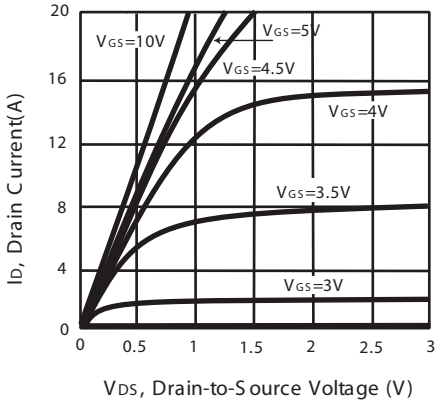


Figure 1. Output Characteristics

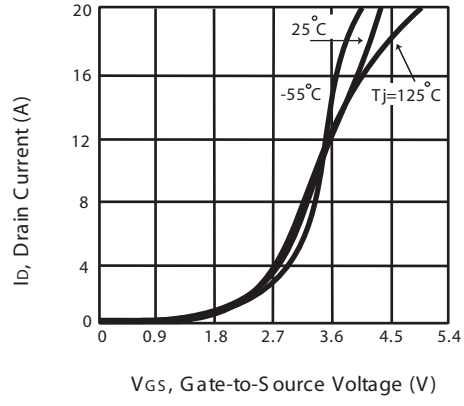


Figure 2. Transfer Characteristics

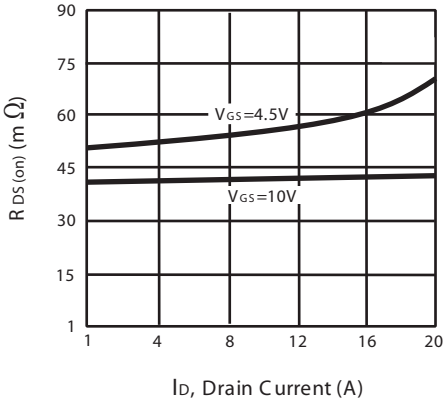


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

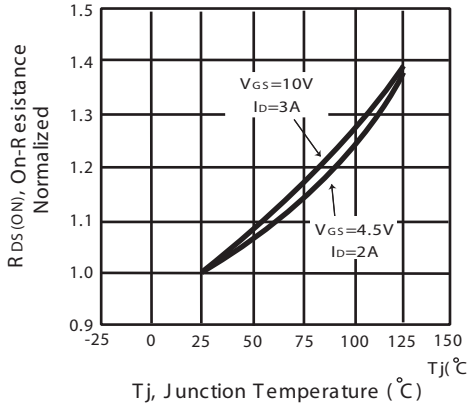


Figure 4. On-Resistance Variation with Drain Current and Temperature

STS3621

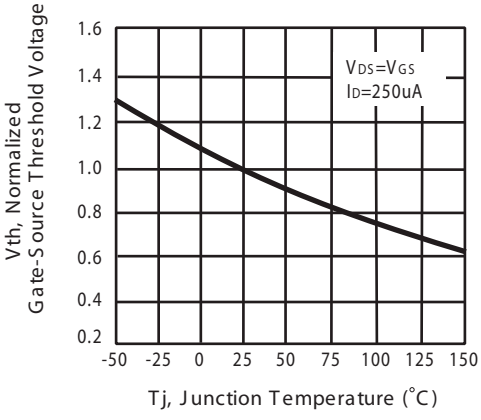


Figure 5. Gate Threshold Variation with Temperature

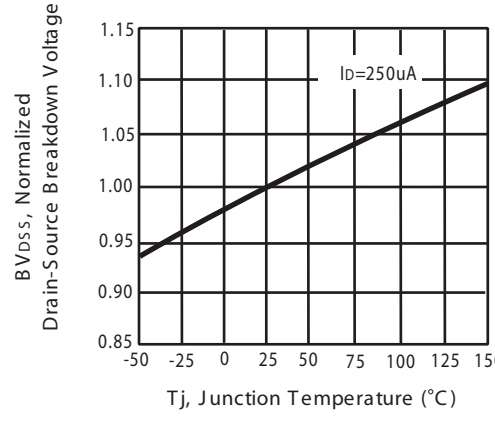


Figure 6. Breakdown Voltage Variation with Temperature

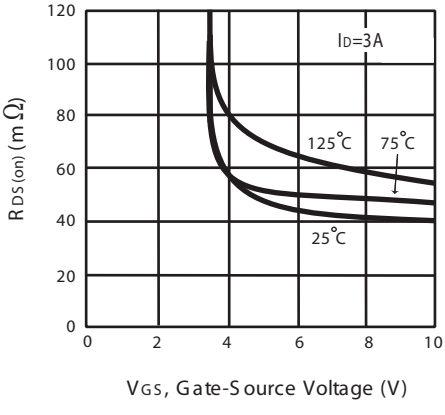


Figure 7. On-Resistance vs. Gate-Source Voltage

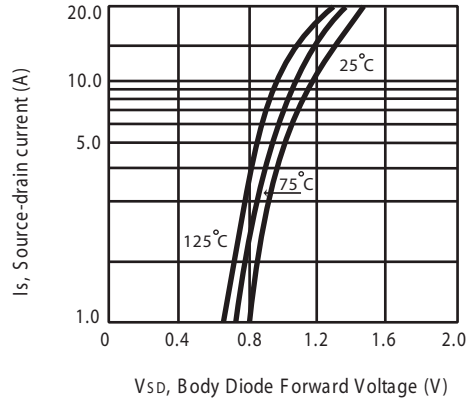


Figure 8. Body Diode Forward Voltage Variation with Source Current

STS3621

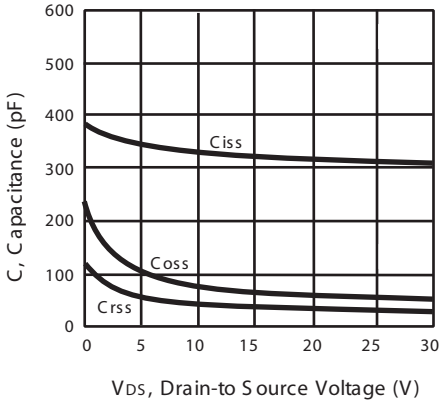


Figure 9. Capacitance

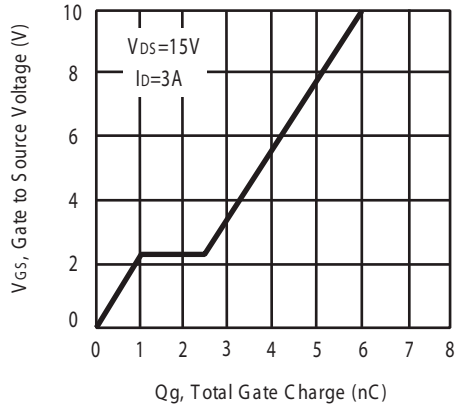


Figure 10. Gate Charge

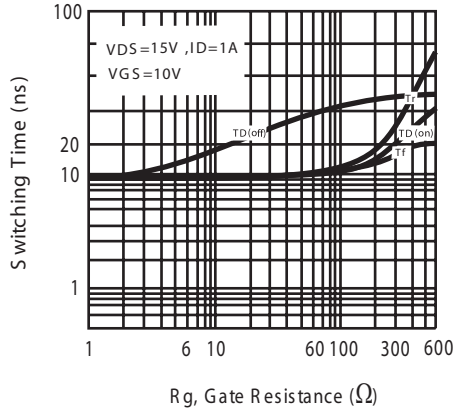


Figure 11.switching characteristics

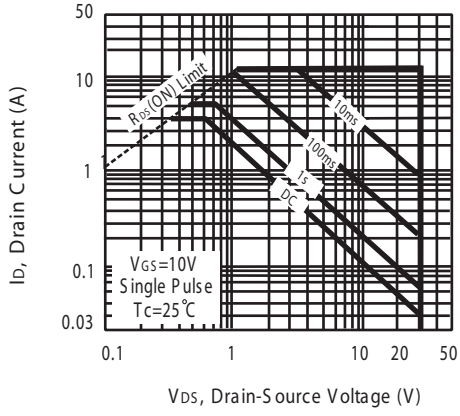
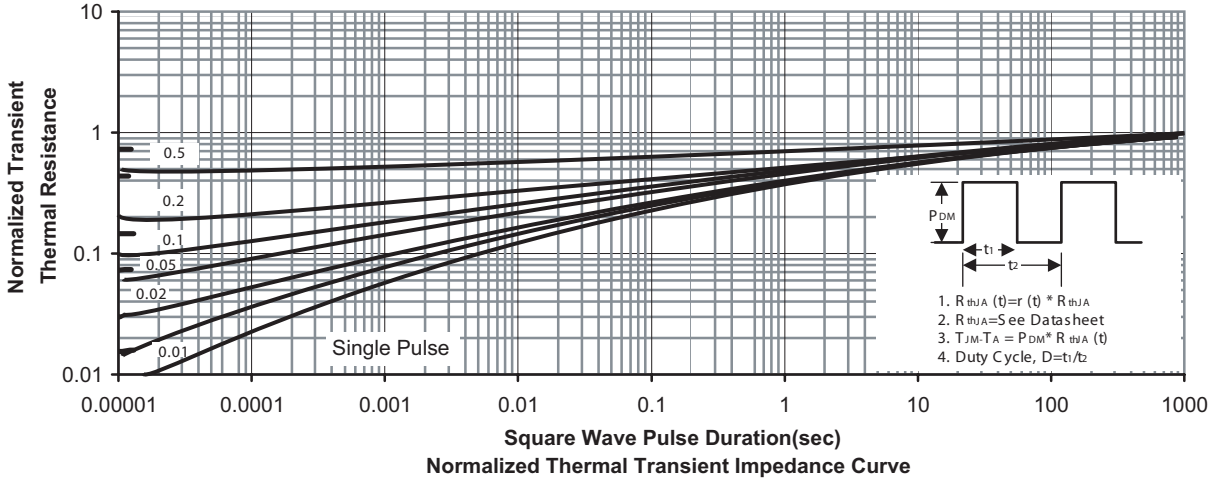


Figure 12. Maximum Safe Operating Area



STS3621

P-Channel

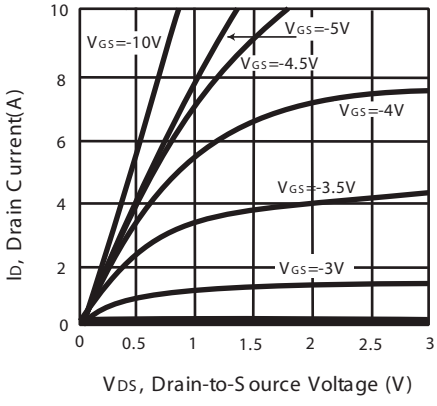


Figure 1. Output Characteristics

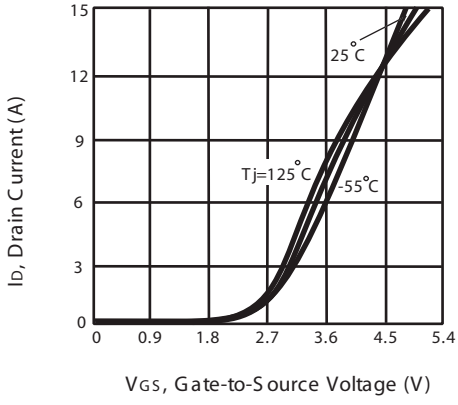


Figure 2. Transfer Characteristics

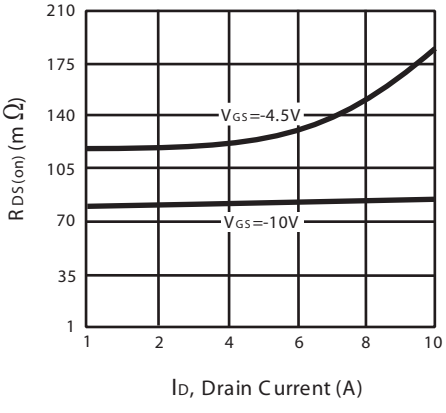


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

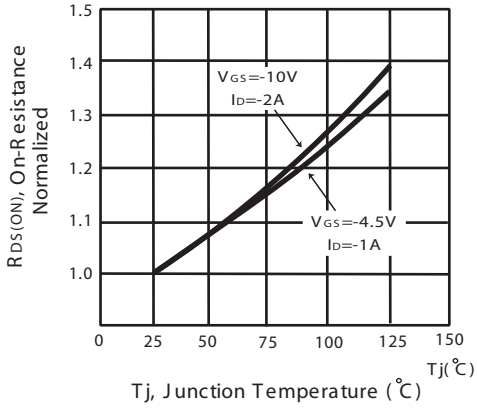


Figure 4. On-Resistance Variation with Drain Current and Temperature

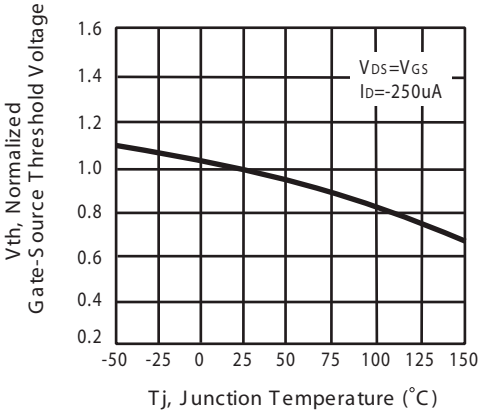


Figure 5. Gate Threshold Variation with Temperature

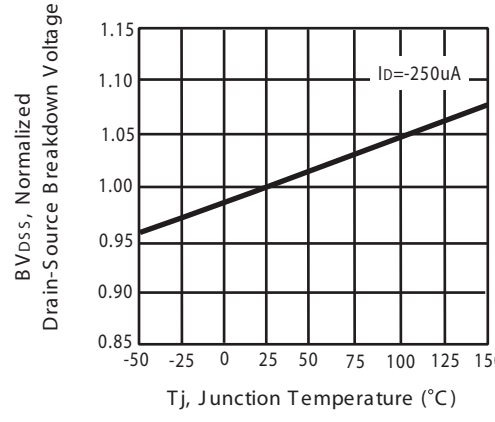


Figure 6. Breakdown Voltage Variation with Temperature

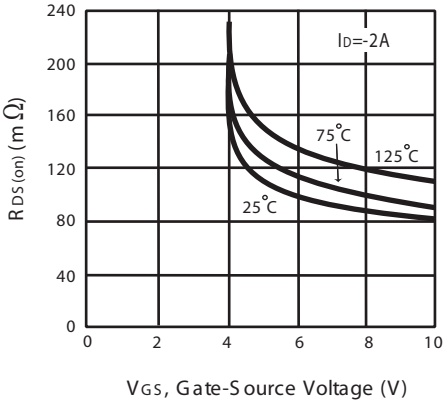


Figure 7. On-Resistance vs. Gate-Source Voltage

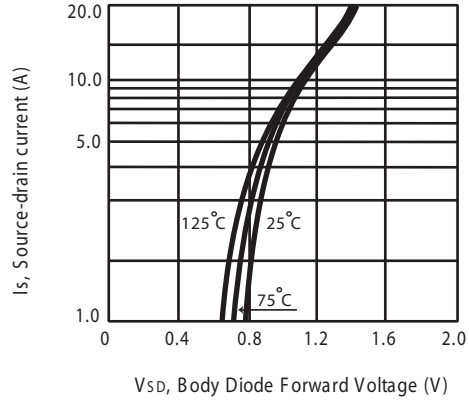


Figure 8. Body Diode Forward Voltage Variation with Source Current

STS3621

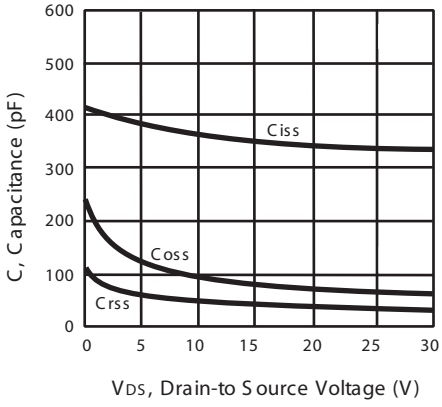


Figure 9. Capacitance

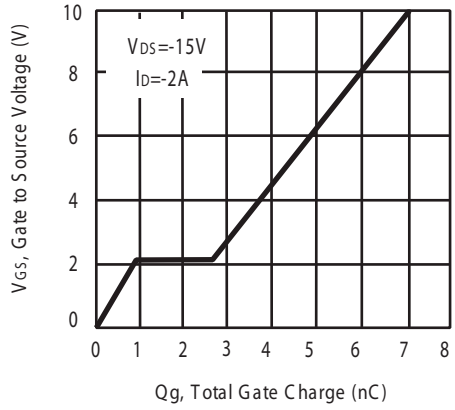


Figure 10. Gate Charge

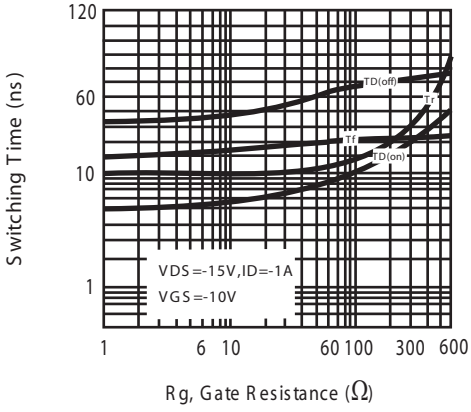


Figure 11.switching characteristics

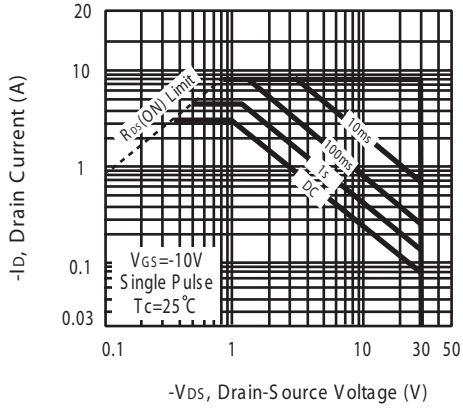
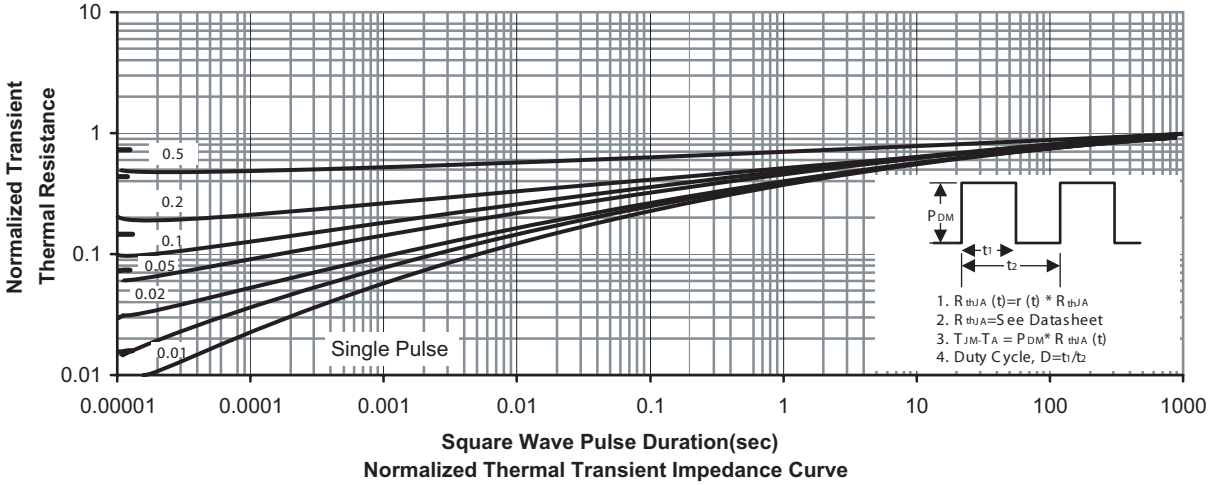
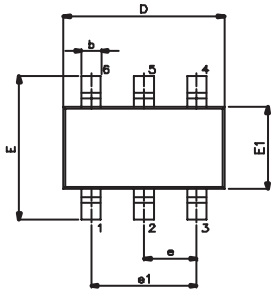


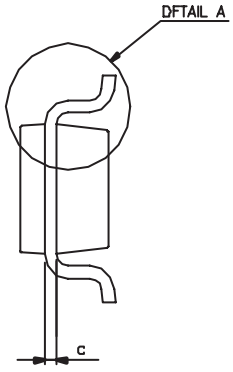
Figure 12. Maximum Safe Operating Area

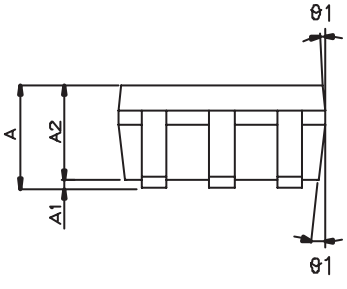


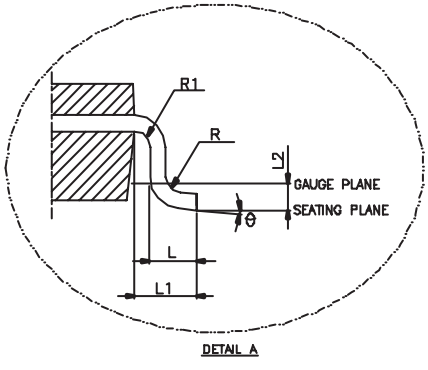
PACKAGE OUTLINE DIMENSIONS

SOT26





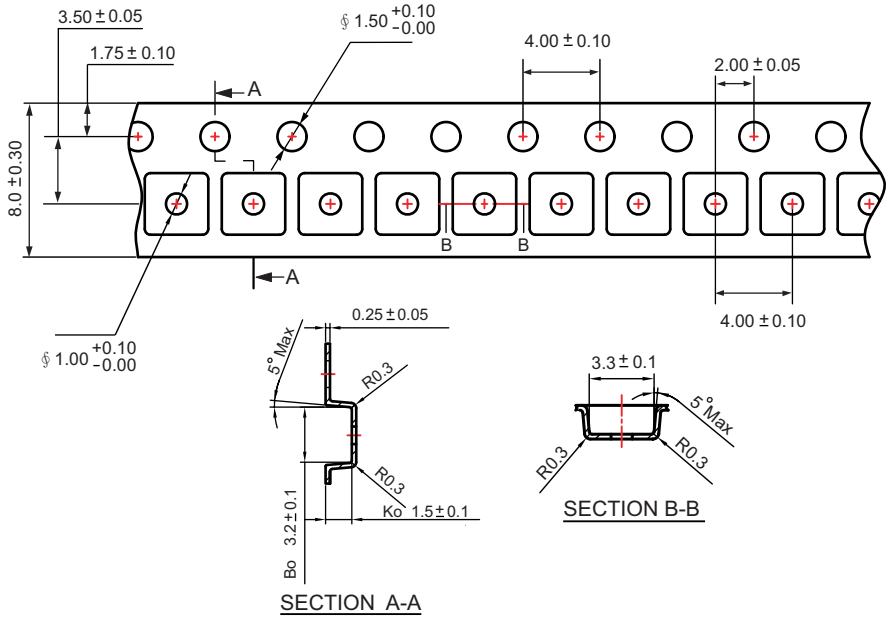




SYMBOL	MIN.	NOM.	MAX.
A	–	–	1.45
A1	–	–	0.15
A2	0.90	1.15	1.30
b	0.30	–	0.50
c	0.08	–	0.22
D		2.90 BSC.	
E		2.80 BSC.	
E1		1.60 BSC.	
e		0.95 BSC	
e1		1.90 BSC.	
L	0.30	0.45	0.60
L1		0.60 REF.	
L2		0.25 BSC.	
R	0.10	–	–
R1	0.10	–	0.25
θ	0°	4°	8°
θ1	5°	10°	15°

SOT 26 Tape and Reel Da

SOT 26 Carrier Tape



SOT 26 Reel